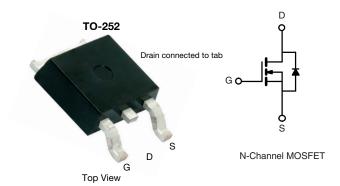


Vishay Siliconix

# Automotive N-Channel 250 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	250		
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.350		
I <sub>D</sub> (A)	7		
Configuration	Single		
Package	TO-252		



#### **FEATURES**

- TrenchFET® power MOSFET
- Package with low thermal resistance
- AEC-Q101 qualified d
- 100 % R<sub>g</sub> and UIS tested
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912



FREE

PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		$V_{DS}$	250	V	
Gate-Source Voltage		$V_{GS}$	± 30	V	
Continuous Drain Current	T <sub>C</sub> = 25 °C	- I <sub>D</sub>	7		
	T <sub>C</sub> = 125 °C		4		
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	50	А	
Pulsed Drain Current b		I <sub>DM</sub>	15		
Single Pulse Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	7		
Single Pulse Avalanche Energy	L = U.1 MH	E <sub>AS</sub>	2.4	mJ	
M. C. D. Division h	T <sub>C</sub> = 25 °C	D	71	W	
Maximum Power Dissipation <sup>b</sup>	T <sub>C</sub> = 125 °C	$P_{D}$	23	VV	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>sta</sub>	-55 to +175	°C	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount c	R <sub>thJA</sub>	50	°C/W
Junction-to-Case (Drain)		$R_{thJC}$	2.1	C/ VV

#### Notes

- a. Package limited.
- b. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- c. When mounted on 1" square PCB (FR4 material).
- d. Parametric verification ongoing.

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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static	1				ı		
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		250	-	-	V
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	= V <sub>GS</sub> , I <sub>D</sub> = 250 μA	2.5	3.0	3.5	V
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$0 \text{ V}, \text{ V}_{GS} = \pm 30 \text{ V}$	-	-	± 100	nA
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 250 V	-	-	1	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 250 V, T <sub>J</sub> = 125 °C	-	-	50	μΑ
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 250 V, T <sub>J</sub> = 175 °C	-	-	250	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	$V_{DS} \ge 5 V$	10	-	-	Α
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 10 A	-	0.290	0.350	
Drain-Source On-State Resistance a	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 10 A, T <sub>J</sub> = 125 °C	-	-	0.858	Ω
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 10 A, T <sub>J</sub> = 175 °C	-	-	1.250	
Forward Transconductance b	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 10 A		-	20	=	S
Dynamic <sup>b</sup>							
Input Capacitance	C <sub>iss</sub>			-	964	1205	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 25 V, f = 1 MHz	-	88	110	pF
Reverse Transfer Capacitance	C <sub>rss</sub>	1		-	32	40	
Total Gate Charge <sup>c</sup>	Qg			-	19	29	
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = 10 V	$V_{DS} = 125 \text{ V}, I_{D} = 10 \text{ A}$	-	6.5	-	nC
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$	1		-	5	-	
Gate Resistance	$R_g$		f = 1 MHz	0.35	1	3	Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			-	9	14	
Rise Time <sup>c</sup>	t <sub>r</sub>	V <sub>DD</sub> =	125 V, $R_L$ = 12.5 $Ω$	-	8	12	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong 10^{\circ} A$ ,	$V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	-	15	23	ns
Fall Time <sup>c</sup>	t <sub>f</sub>	7		-	4	6	
Source-Drain Diode Ratings and Chara	cteristics <sup>b</sup>						
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	15	Α
Forward Voltage	V <sub>SD</sub>	I <sub>F</sub> = 20 A, V <sub>GS</sub> = 0 V		_	0.9	1.5	V

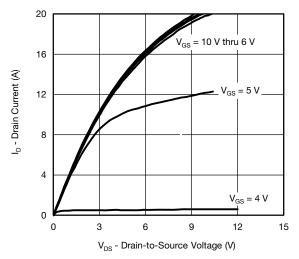
#### Notes

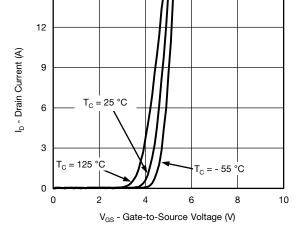
- a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



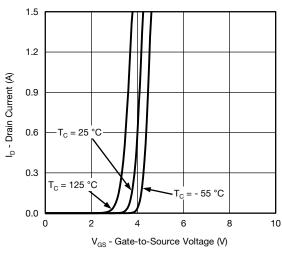
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)

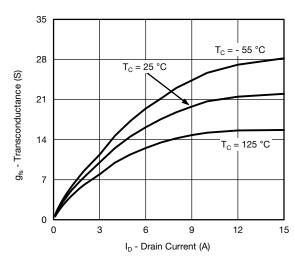




#### **Output Characteristics**

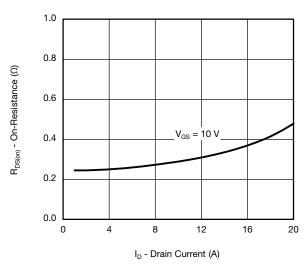
**Transfer Characteristics** 

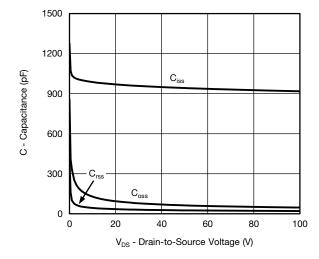




### Transfer Characteristics

Transconductance





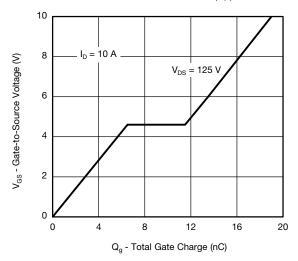
On-Resistance vs. Drain Current

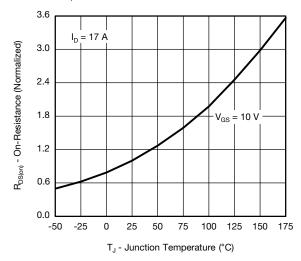
Capacitance

For technical questions, contact: automostechsu



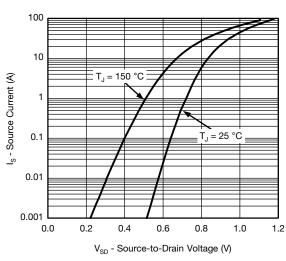
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)

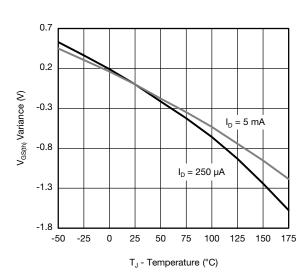




#### **Gate Charge**

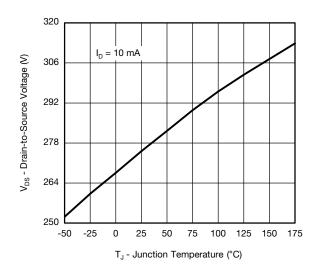






## Source Drain Diode Forward Voltage

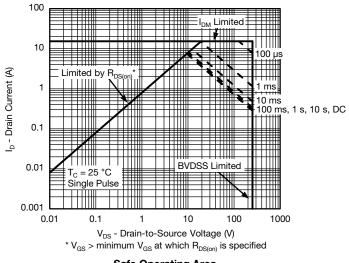
#### Threshold Voltage



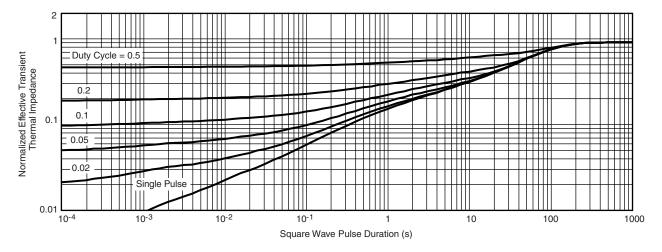
Drain Source Breakdown vs. Junction Temperature



## **THERMAL RATINGS** ( $T_A = 25$ °C, unless otherwise noted)



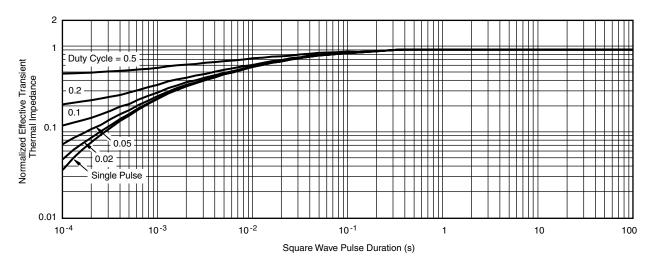
#### Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

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## THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



#### Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg267088">www.vishay.com/ppg267088</a>.



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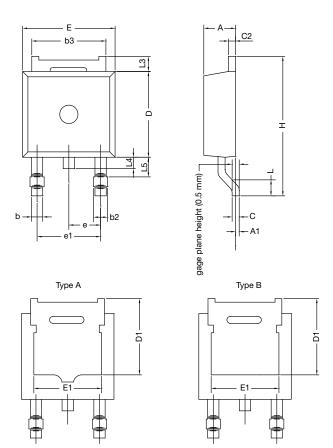
REVISION	HISTORY a	
REVISION	DATE	DESCRIPTION OF CHANGE
С	04-Aug-15	Revised R <sub>g</sub> minimum limit

#### Note

a. As of April 2014



## **TO-252AA Case Outline**



DIM.	MILLIMETERS		INCHES	
DIIVI.	MIN.	MAX.	MIN.	MAX.
Α	2.18	2.38	0.086	0.094
A1	-	0.127	-	0.005
b	0.64	0.88	0.025	0.035
b2	0.76	1.14	0.030	0.045
b3	4.95	5.46	0.195	0.215
С	0.46	0.61	0.018	0.024
C2	0.46	0.89	0.018	0.035
D	5.97	6.22	0.235	0.245
D1	4.10	-	0.161	-
E	6.35	6.73	0.250	0.265
E1	4.32	-	0.170	-
Н	9.40	10.41	0.370	0.410
е	2.28	BSC	0.090 BSC	
e1	4.56	BSC	0.180	BSC
L	1.40	1.78	0.055	0.070
L3	0.89	1.27	0.035	0.050
L4	-	1.02	-	0.040
L5	1.01	1.52	0.040	0.060

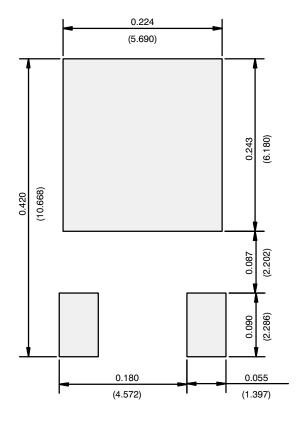
# ECN: T25-0122-Rev. C, 12-May-2025 DWG: 6019

#### Notes

- Dimension L3 is for reference only
- Dimension D1 and E1 on type A and B is the same



## **RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)**



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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